



### 100V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

100 V

Current

170 mA

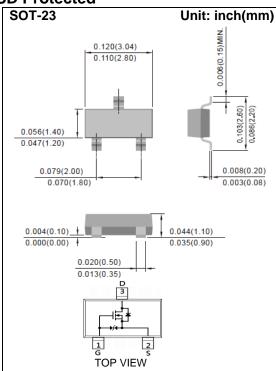
#### **Features**

- RDS(ON), VGS@10V, ID@170mA<6Ω
- RDS(ON), VGS@4.5V, ID@130mA<10Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-23 Package

• Terminals: Solderable per MIL-STD-750, Method 2026



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	170	mA
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	680	mA
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	500	mW
	Derate above 25°C		4	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	ο°
Typical Thermal Resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	250	°C/W





### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.7	2.5	V		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =170mA	-	4	6	Ω		
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =130mA	-	4.5	10			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	uA		
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA		
Dynamic (Note 5)								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =30V, I <sub>D</sub> =170mA, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	1.8	-	nC		
Gate-Source Charge	$Q_{gs}$		-	0.4	-			
Gate-Drain Charge	$Q_{gd}$		-	0.3	-			
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	45	-	pF		
Output Capacitance	Coss		-	14	-			
Reverse Transfer Capacitance	Crss		-	7.8	-			
Turn-On Delay Time	td <sub>(on)</sub>	)/ 00\/ L 470 ·· A	-	3.4	-	ns		
Turn-On Rise Time	tr	$V_{DD}$ =30V, $I_{D}$ =170mA, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	19	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	8.2	-			
Turn-Off Fall Time	tf		-	20	-			
Drain-Source Diode								
Maximum Continuous Drain-Source				-	170	mA		
Diode Forward Current	I <sub>S</sub>							
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =170mA, V <sub>GS</sub> =0V	-	0.9	1.3	V		

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

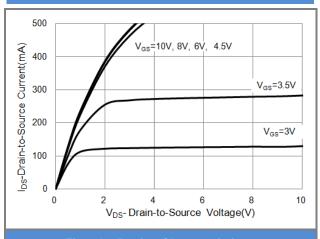
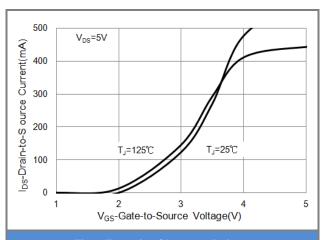


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

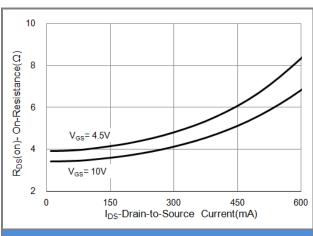


Fig.3 On-Resistance vs. Drain Current

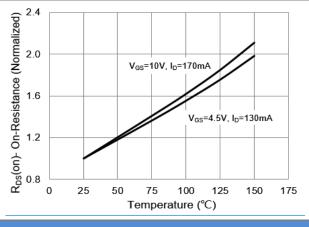


Fig.4 On-Resistance vs. Junction temperature

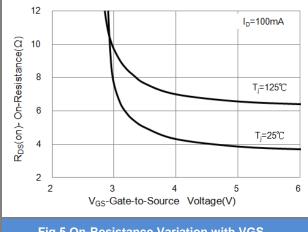
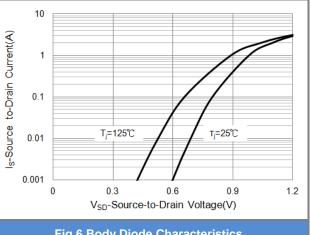


Fig.5 On-Resistance Variation with VGS.

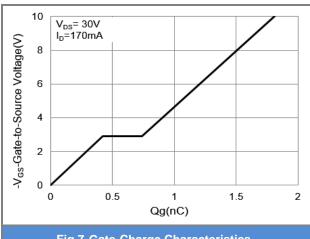


**Fig.6 Body Diode Characteristics** 





### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

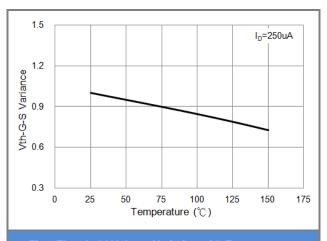


Fig.8 Threshold Voltage Variation with Temperature

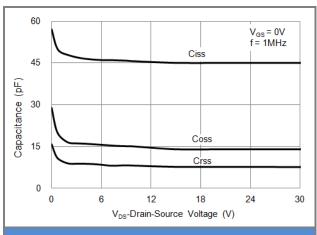


Fig.9 Capacitance vs. Drain-Source Voltage

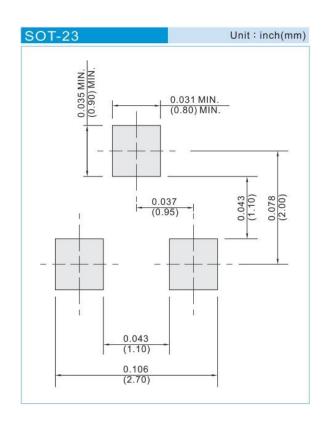




### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing Type	Marking	Version
BSS123_R1_00001	SOT-23	3K pcs / 7" reel	A76	Halogen free
BSS123_R2_00001	SOT-23	12K pcs / 13" reel	A76	Halogen free

### **MOUNTING PAD LAYOUT**







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